

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Package	I _D T _A = +25°C (Notes 4 & 6)
-60V	85mΩ @ V _{GS} = -10V	SO-8	-3.9A
	125mΩ @ V _{GS} = -4.5V		-3.2A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

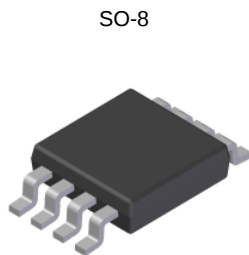
- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features

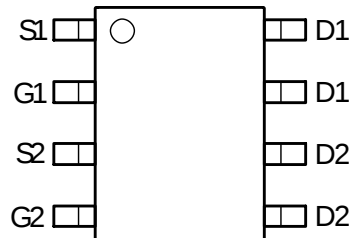
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Profile SOIC Package
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([ZXMP6A16DN8Q](#))**

Mechanical Data

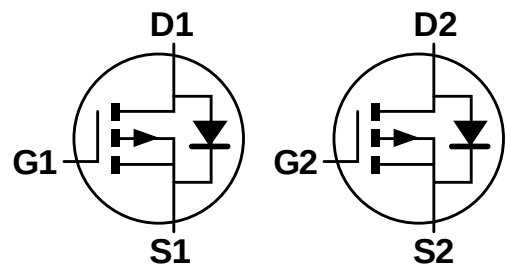
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe.
Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.074 grams (Approximate)



Top View



Top View



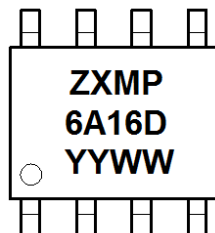
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMP6A16DN8TA	SO-8	500/Tape & Reel
ZXMP6A16DN8TC	SO-8	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



ZXMP6A16D = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

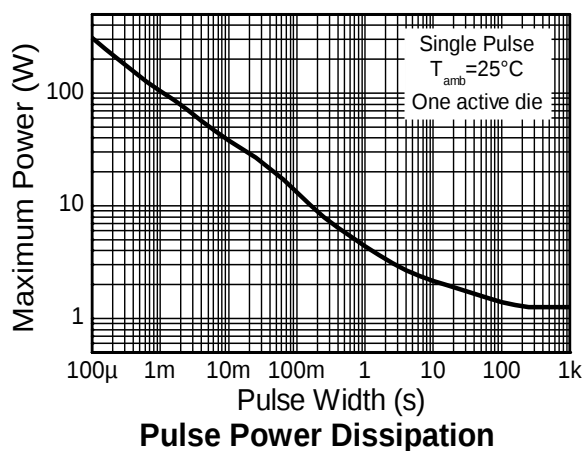
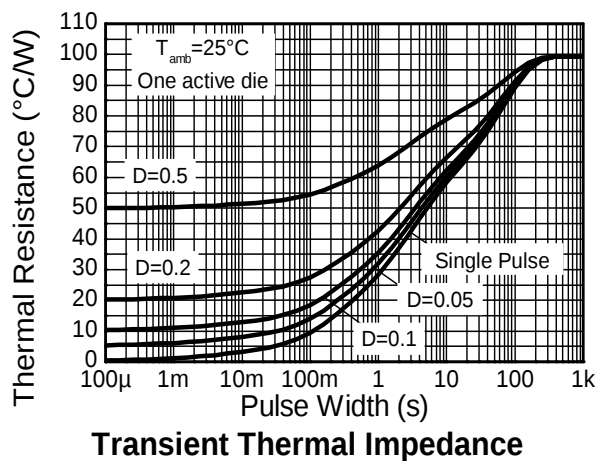
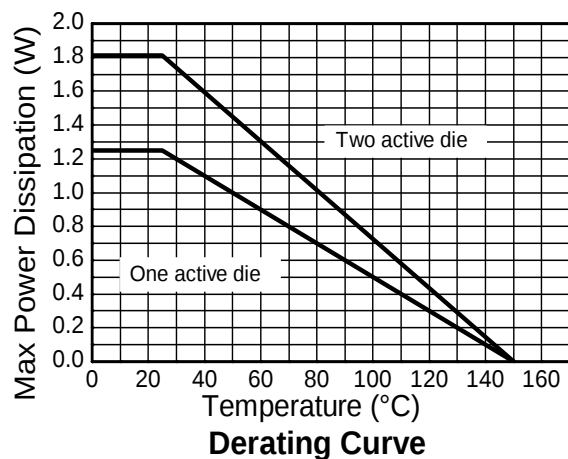
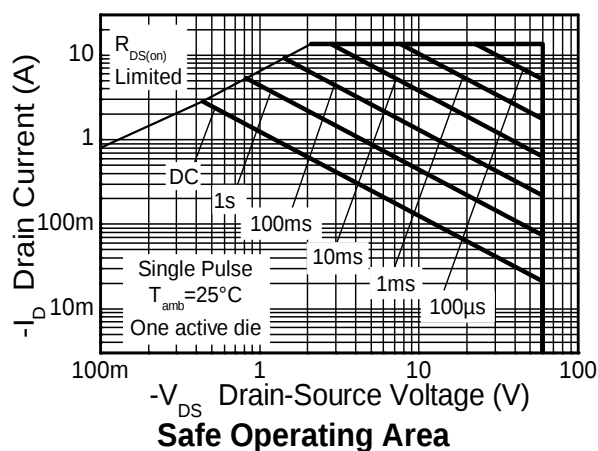
Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-60	V
Gate-Source Voltage		(Note 5)	V _{GS}	±20	V
Continuous Drain Current	V _{GS} = 10V	(Notes 7 & 9)	I _D	-3.9	A
		T _A = +70°C (Notes 7 & 9)		-3.1	
		(Notes 6 & 9)		-2.9	
Pulsed Drain Current		(Notes 8 & 9)	I _{DM}	-18.3	A
Continuous Source Current (Body Diode)		(Notes 7 & 9)	I _S	-3.2	A
Pulsed Source Current (Body Diode)		(Notes 8 & 9)	I _{SM}	-18.3	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Notes 6 & 9)	P _D	1.25	W mW/°C
	(Notes 6 & 10)		10.0	
	(Notes 7 & 9)		1.81	
	(Notes 6 & 10)		14.5	
Thermal Resistance, Junction to Ambient	(Notes 6 & 9)	R _{θJA}	2.15	°C/W
	(Notes 6 & 10)		17	
	(Notes 7 & 9)		100	
Thermal Resistance, Junction to Lead	(Notes 6 & 10)	R _{θJL}	70	°C/W
	(Notes 7 & 9)		60	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes:
5. AEC-Q101 V_{GS} maximum is ±16V.
 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 7. Same as Note (5), except the device is measured at t ≤ 10 sec.
 8. Same as Note (5), except the device is pulsed with D = 0.02 and pulse width 300μs.
 9. For a dual device with one active die.
 10. For a device with two active die running at equal power.
 11. Thermal resistance from junction to solder-point.

Thermal Characteristics (Continued)

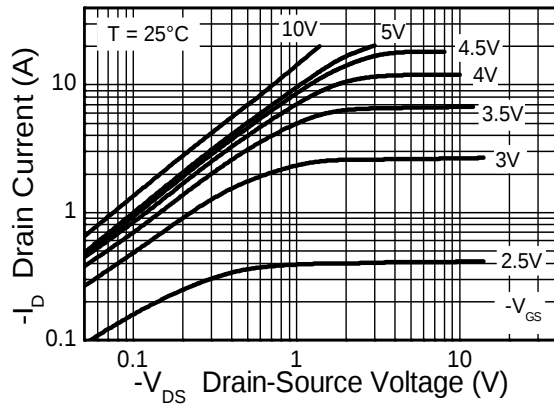


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

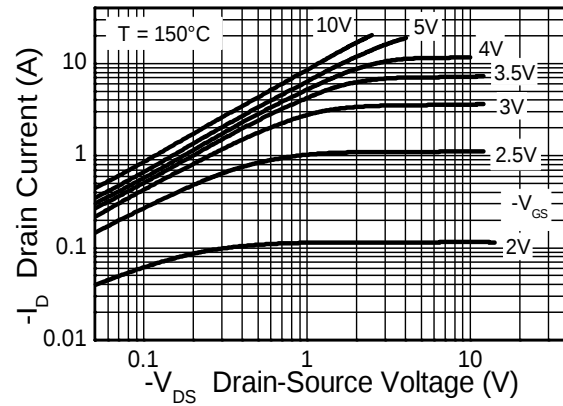
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	I _D = -250μA, V _{GS} = 0V	
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	μA	V _{DS} = -60V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	—	V	I _D = -250μA, V _{DS} = V _{GS}	
Static Drain-Source On-Resistance (Note 12)	R _{DS(ON)}	—	—	85	mΩ	V _{GS} = -10V, I _D = -2.9A	
			—	125		V _{GS} = -4.5V, I _D = -2.4A	
Forward Transconductance (Notes 12 & 13)	g _{FS}	—	7.2	—	S	V _{DS} = -15V, I _D = -2.9A	
Diode Forward Voltage (Note 12)	V _{SD}	—	-0.85	-0.95	V	I _S = -3.4A, V _{GS} = 0V, T _J = +25°C	
Reverse Recovery Time (Note 13)	t _{RR}	—	29.2	—	ns	I _S = -2A, di/dt = 100A/μs, T _J = +25°C	
Reverse Recovery Charge (Note 13)	Q _{RR}	—	39.6	—	nC		
DYNAMIC CHARACTERISTICS (Note 14)							
Input Capacitance	C _{ISS}	—	1,021	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	C _{OSS}	—	83.1	—	pF		
Reverse Transfer Capacitance	C _{RSS}	—	56.4	—	pF		
Total Gate Charge	Q _G	—	12.1	—	nC	V _{GS} = -5V	V _{DS} = -30V, I _D = -2.9A
Total Gate Charge	Q _G	—	24.2	—	nC	V _{GS} = -10V	
Gate-Source Charge	Q _{GS}	—	2.5	—	nC		
Gate-Drain Charge	Q _{GD}	—	3.7	—	nC		
Turn-On Delay Time	t _{D(ON)}	—	3.5	—	ns	V _{DD} = -30V, V _{GS} = -10V, I _D = -1A, R _G ≅ 6.0Ω	
Turn-On Rise Time	t _R	—	4.1	—	ns		
Turn-Off Delay Time	t _{D(OFF)}	—	35	—	ns		
Turn-Off Fall Time	t _F	—	10	—	ns		

Notes: 12. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
13. For design aid only, not subject to production testing.
14. Switching characteristics are independent of operating junction temperatures.

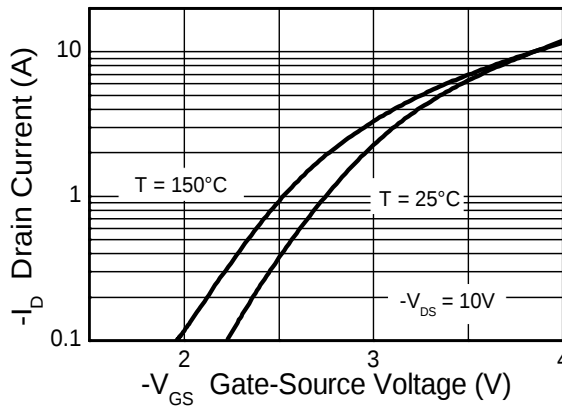
Typical Characteristics



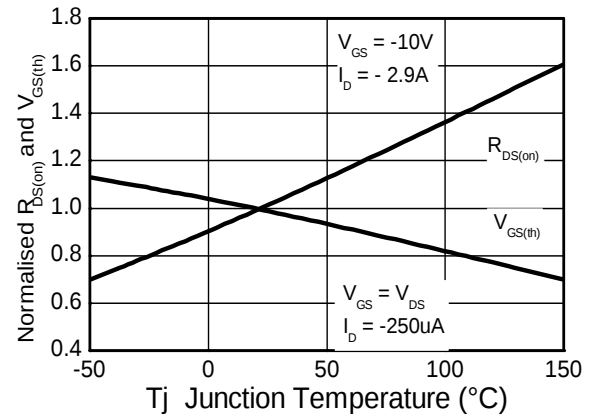
Output Characteristics



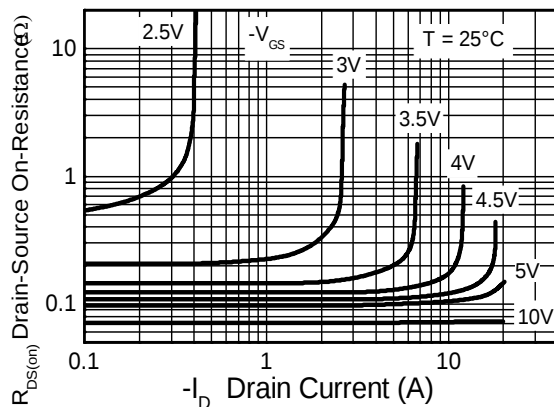
Output Characteristics



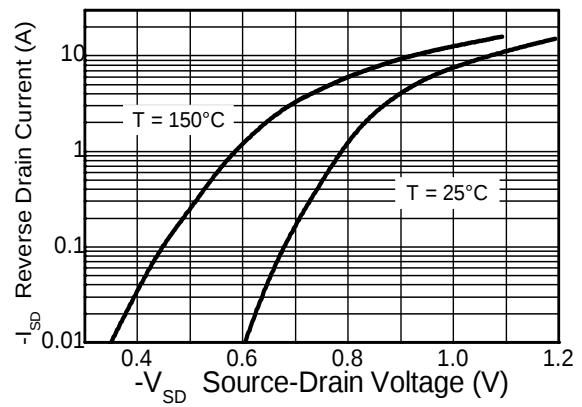
Typical Transfer Characteristics



Normalised Curves v Temperature

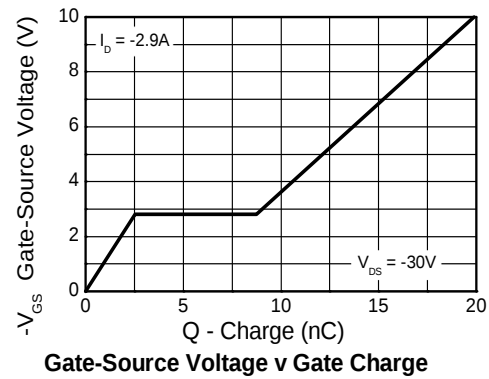
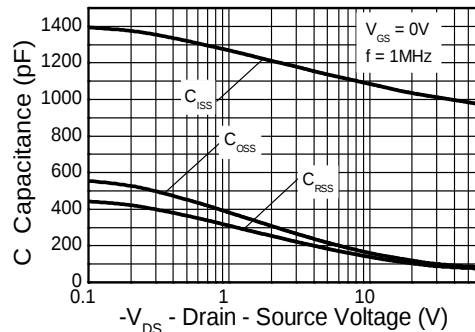


On-Resistance v Drain Current

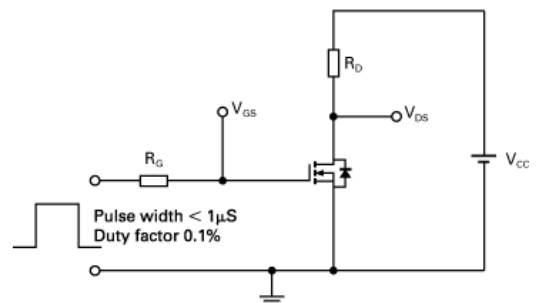
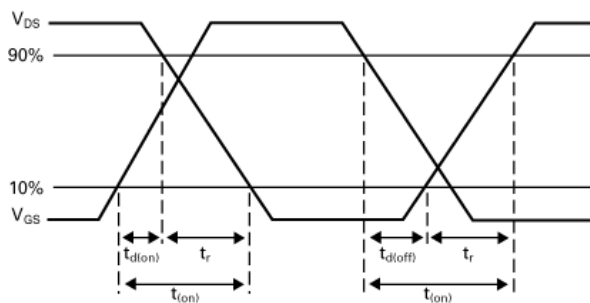
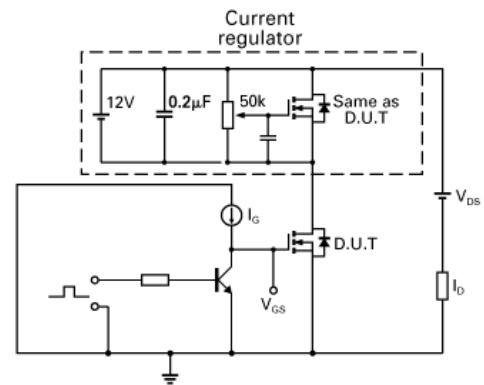
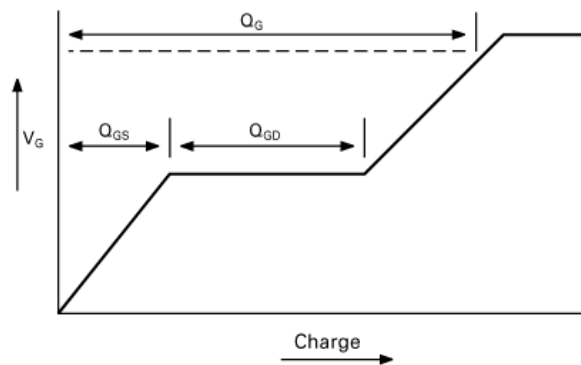


Source-Drain Diode Forward Voltage

Typical Characteristics (Continued)



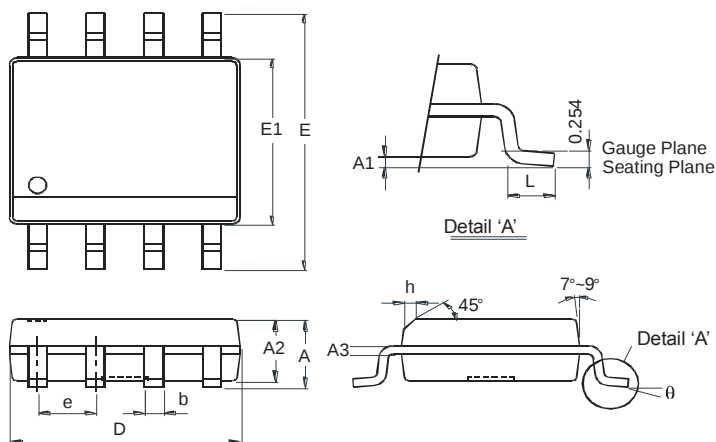
Test Circuits



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

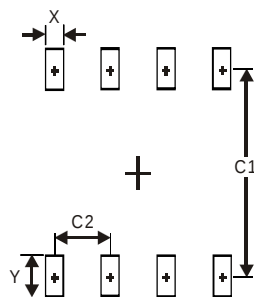


SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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